

isc Silicon NPN Power Transistor

2SC6090

DESCRIPTION

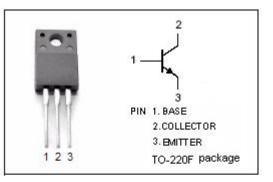
- Collector-Base Breakdown Voltage-
- : V_{(BR)CEO}= 1500V (Min)
- High Speed Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

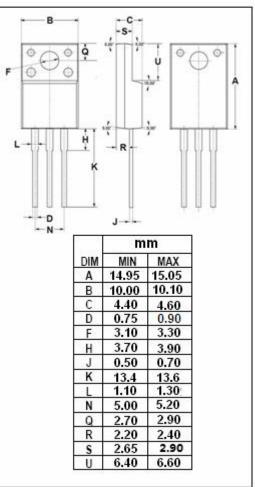
APPLICATIONS

Designed for Color TV horizontal deflection output applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER	VALUE	UNIT					
Collector-Base Voltage	1500	v					
Collector-Emitter Voltage	700	V					
Emitter-Base Voltage	5	V					
Collector Current-Continuous	10	А					
Collector Current-Pulse	25	А					
Collector Power Dissipation @ $T_a=25^{\circ}C$	2						
Collector Power Dissipation @ T _C =25°C	35	W					
Junction Temperature	150	°C					
stg Storage Temperature Range -55~1		°C					
	PARAMETER Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current-Continuous Collector Current-Pulse Collector Power Dissipation @ Ta=25°C Collector Power Dissipation @ Tc=25°C Junction Temperature	PARAMETERVALUECollector-Base Voltage1500Collector-Emitter Voltage700Emitter-Base Voltage5Collector Current-Continuous10Collector Current-Pulse25Collector Power Dissipation @ Ta=25°C2Collector Power Dissipation @ Tc=25°C35Junction Temperature150					

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA; I _B = 0	700			v
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 7.2A; I _B = 1.44A			3.0	v
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I _C = 7.2A; I _B = 1.44A			1.5	v
I _{CBO}	Collector Cutoff Current	V _{CB} =800V; I _E = 0			10	μ Α
I _{CES}	Collector Cutoff Current	V _{CE} =1500V; R _{BE} = 0			1.0	mA
Іево	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0			1.0	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	15			
h _{FE-2}	DC Current Gain	I _C = 8A; V _{CE} = 5V	5		7	
Switching ti	mes					<u>.</u>
tr	Fall Time	I _C = 5A; I _{B1} = 1A; I _{B2} = -2A			0.2	μ S

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